Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- MLPAK33 package (3.3 x 3.3 mm footprint)

3. Applications

- · High-side load switch
- Battery management
- DC-to-DC conversion
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage			-25	-	25	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	-15.2	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state	V_{GS} = -10 V; I_D = -9 A; T_j = 25 °C		-	11.1	12.8	mΩ
	resistance	V_{GS} = -4.5 V; I_D = -7.6 A; T_j = 25 °C		-	14.5	17.7	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



30 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	1 2 3 4	
2	S	source	رف-ق-ق	
3	S	source		D
4	G	gate		
5	D	drain		
6	D	drain	Raaay	Ś 017aaa257
7	D	drain	8 7 6 5 MI DAK 22 (SOT 2002 4)	
8	D	drain	MLPAK33 (SOT8002-1)	

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
PXP012-30QL		plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body	SOT8002-1				

7. Marking

Table 4. Marking codes

Type number	Marking code
PXP012-30QL	9AU

30 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-25	25	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-15.2	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-8.9	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-5.7	Α
		V _{GS} = -10 V; T _{sp} = 25 °C		-	-38.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-62.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; t ≤ 5 s	[1]	-	4.8	W
		T _{amb} = 25 °C	[1]	-	1.7	W
		T _{sp} = 25 °C		-	32	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode		'	'		
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.7	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

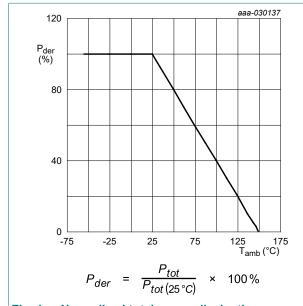


Fig. 1. Normalized total power dissipation as a function of ambient temperature

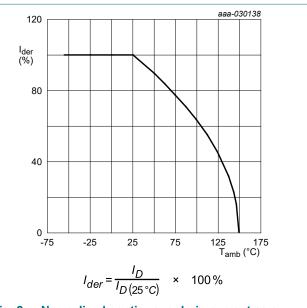


Fig. 2. Normalized continuous drain current as a function of ambient temperature

30 V, P-channel Trench MOSFET

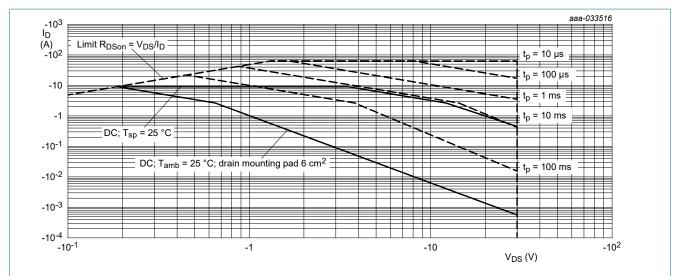


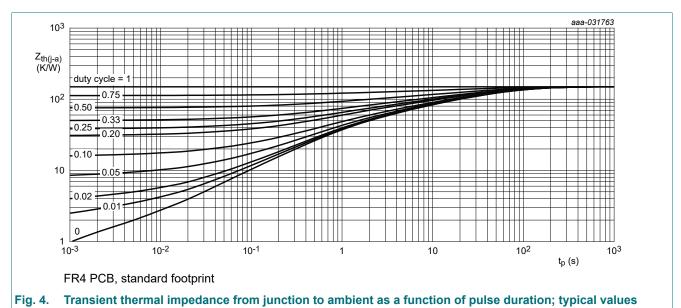
Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

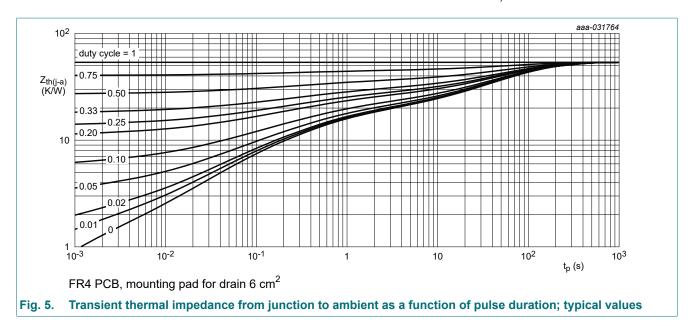
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	150	190	K/W
ju	junction to ambient		[2]	-	60	75	K/W
		in free air; t ≤ 5 s	[2]	-	21	26	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	2.5	4	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



30 V, P-channel Trench MOSFET



30 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 °C$	-1	-1.5	-2	V
I _{DSS}	drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -9 \text{ A}; T_j = 25 \text{ °C}$	-	11.1	12.8	mΩ
	resistance	V_{GS} = -10 V; I_D = -9 A; T_j = 150 °C	-	18	20.7	mΩ
		$V_{GS} = -4.5 \text{ V}; I_D = -7.6 \text{ A}; T_j = 25 \text{ °C}$	-	14.5	17.7	mΩ
9fs	forward transconductance	V_{DS} = -10 V; I_D = -9 A; T_j = 25 °C	-	25	-	S
R_G	gate resistance	f = 1 MHz	-	20.3	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -9 A; V_{GS} = -10 V; T_{j} = 25 °C	-	28.9	43.4	nC
		V_{DS} = -15 V; I_D = -7.6 A; V_{GS} = -4.5 V;	-	14.1	21.2	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	3.3	-	nC
Q _{GS(th)}	pre-threshold gate- source charge		-	2.1	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	1.2	-	nC
Q _{GD}	gate-drain charge	1	-	5.3	-	nC
V_{GSpl}	gate-source plateau voltage	$V_{DS} = -15 \text{ V}; I_D = -7.6 \text{ A}; T_j = 25 \text{ °C}$	-	-2.4	-	V
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	1400	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	170	-	pF
C _{rss}	reverse transfer capacitance		-	140	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -15 V; I_D = -7.6 A; V_{GS} = -4.5 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$; $T_j = 25 °C$	-	27	-	ns
t _{d(off)}	turn-off delay time]	-	68	-	ns
t _f	fall time]	-	55	-	ns
Source-drai	n diode			•		
V _{SD}	source-drain voltage	$I_S = -1.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-0.6	-1.2	V
t _{rr}	reverse recovery time	$I_S = -1.7 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$;	-	13	-	ns
Q _r	recovered charge	$V_{GS} = -4.5 \text{ V}; V_{DS} = -15 \text{ V}; T_j = 25 \text{ °C}$	-	4	-	nC
t _a	reverse recovery rise time		-	7	-	ns
t _b	reverse recovery fall time		-	6	-	ns

30 V, P-channel Trench MOSFET

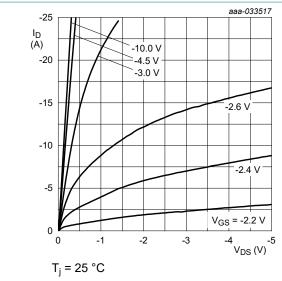


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

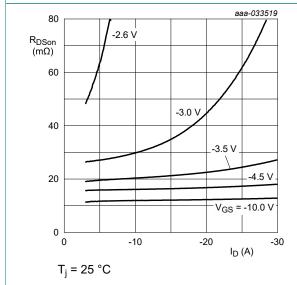


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

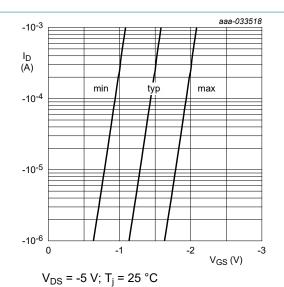


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

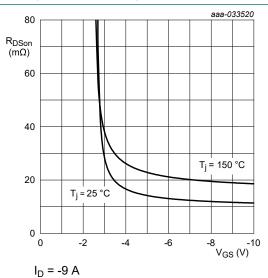


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

30 V, P-channel Trench MOSFET

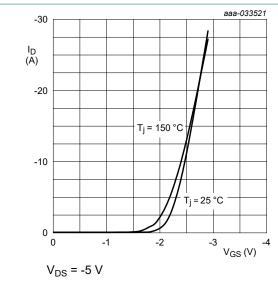


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

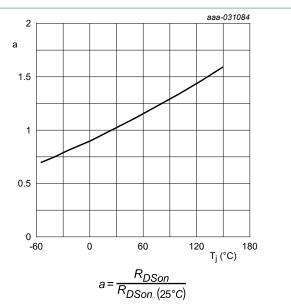


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature; typical values

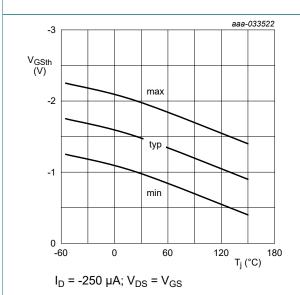


Fig. 12. Gate-source threshold voltage as a function of junction temperature

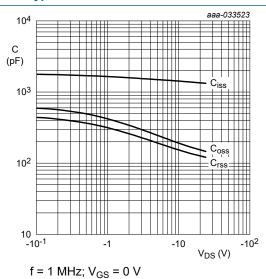


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

values

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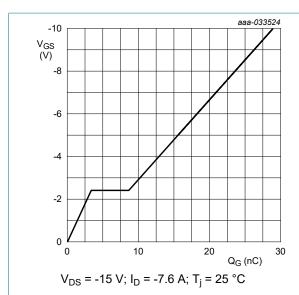


Fig. 14. Gate-source voltage as a function of gate charge; typical values

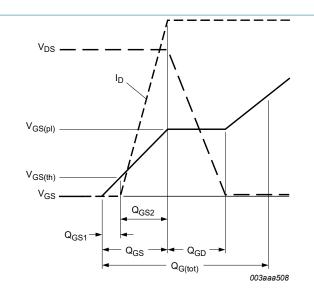


Fig. 15. Gate charge waveform definitions

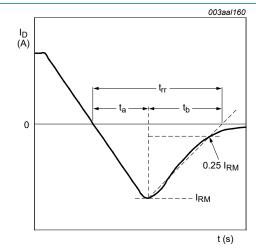


Fig. 16. Reverse recovery timing definition

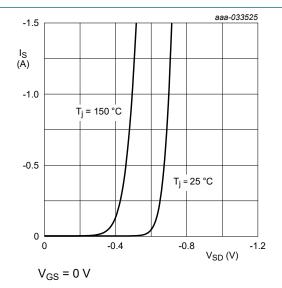
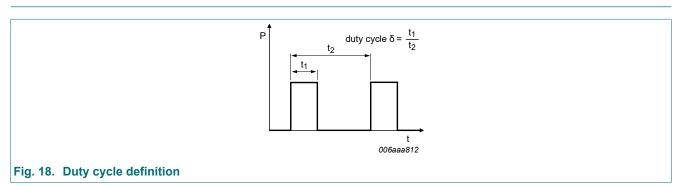


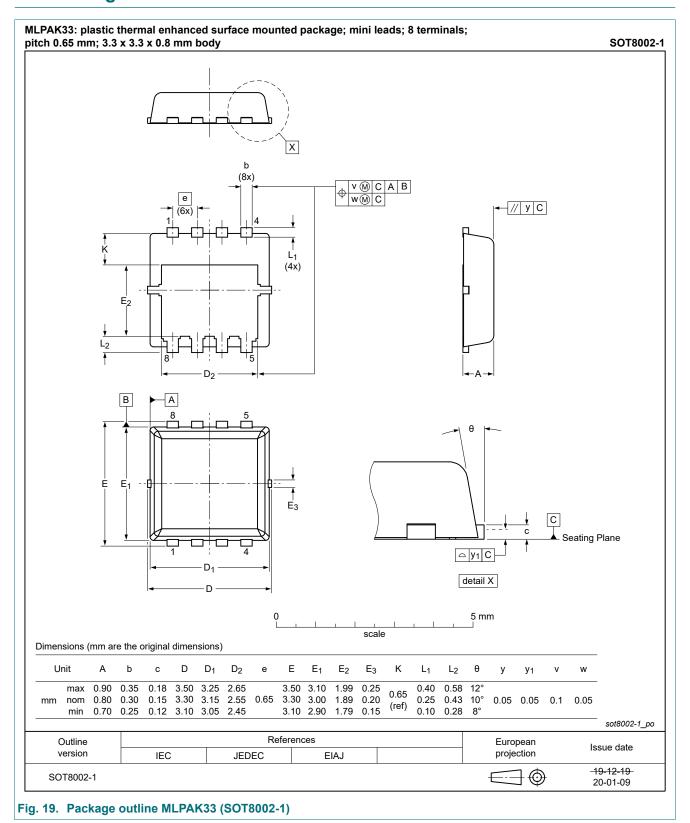
Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information



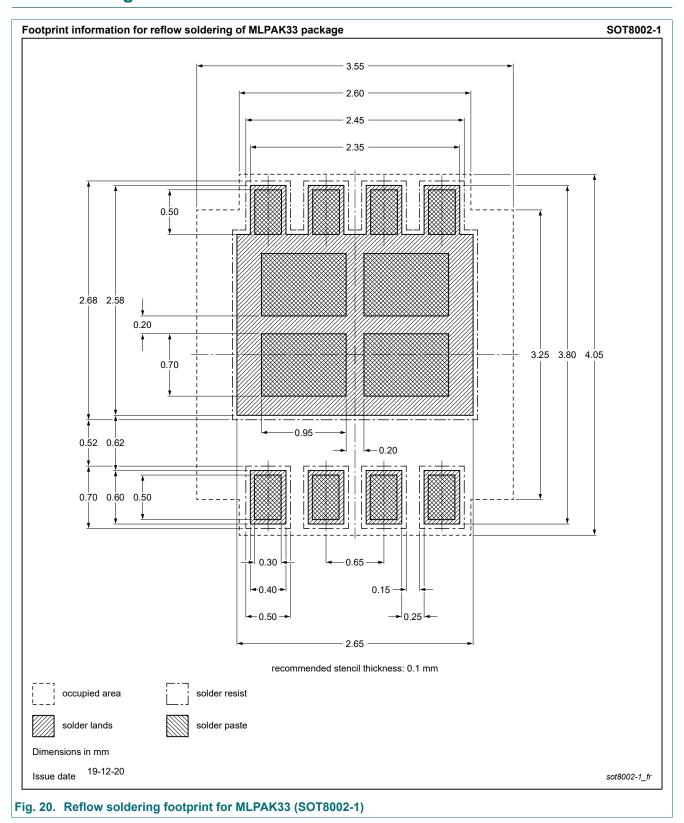
30 V, P-channel Trench MOSFET

12. Package outline



30 V, P-channel Trench MOSFET

13. Soldering



30 V, P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PXP012-30QL v.1	20220119	Product data sheet	-	-

30 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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30 V, P-channel Trench MOSFET

Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	4
10. Characteristics	6
11. Test information	9
12. Package outline	10
13. Soldering	11
14. Revision history	12
15. Legal information	13

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WMJ80N60C4 BXP2N20L BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR DMNH15H110SK3-13
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